

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Xia, et al.

Serial No.: 10/632,179

Confirmation No.: Unknown

Filed:

July 31, 2003

For:

Method of Decreasing the

K Value in SIOC Layer Deposited by Chemical

Vapor Deposition

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

Cra

Group Art Unit: Unknown

Examiner:

Unknown

CERTIFICATE OF MAILING

37 CFR 1.8

I hereby certify that this correspondence is being deposited on 1/1/8, 2003 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.

11/18/03

Signature

## INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/2592.C6/KMT.

Respectfully submitted,

Keith M. Tackett

Registration No. 32,008

MOSER, PATTERSON & SHERIDAN, L.L.P.

3040 Post Oak Blvd., Suite 1500

Houston, TX 77056

Telephone: (713) 623-4844 Facsimile: (713) 623-4846 Attorney for Applicant(s)

U.S. Depar	tment o	f Commerce, Pat	ent and Trade	mark Office	Docket N	lo.	Sheet 3 of Serial No		
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT							Confirma Unknown		
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	A26	5,703,404	12/30/1997	Matsuura	25,7	758	12/24/1996	3	
	A27	5,700,720	12/23/1997	Hashimoto	438	622	12/20/1995	5	
	A28	5,693,563	12/02/1997	Teong	437	190	07/15/1996	6	
	A29	5,683,940	11/04/1997	Yashiro	438	760	12/20/1995	5	
	A30	5,679,413	10/21/1997	Petrmichle, et al.	427	534	10/11/1996	6	
	A31	5,638,251	06/10/1997	Goel, et al.	361	313	10/03/1995	5	
	A32	5,637,351	06/10/1997	O'Neal, et al.	427	255.37	05/11/1995	5	
	A33	5,618,619	04/08/1997	Petrmichl, et al.	428	334	03/03/1994	}	
	A34	5,616,369	04/01/1997	Williams, et al.	427	560	06/24/1994	ļ 	
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	A36	5,593,741	01/14/1997	Ikeda	427	579	06/28/1995	5	
	A37	5,578,523	11/26/1996	Fiordalice, et al.	438	633	05/18/1995	5	
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	A58	5,224,441	07/06/1993	Felts, et al.	118	718	09/27/1991		
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	A65	4,981,724	01/01/1991	Hochberg, et al.	427	255.3	10/27/1988	3	
	A66	4,973,511	11/27/1990	Farmer, et al.	428	216	12/01/1998	3	
	A67	4,900,591	02/13/1990	Bennett, et al.	427	255	01/20/1988	3	
	A68		01/16/1990	Lane, et al. Mitchener	437	238	10/26/1988	3	
	A69		07/04/1989		437	238	06/29/1987	7	
	A70	4,828,880	05/09/1989	Jenkins, et al.	427	167	12/21/1987	7	
	A71	4,824,690	04/25/1989	Heinecke, et al.	427	38	11/03/1987	7	
	A72	4,812,325	03/14/1989	Ishihara, et al.	427	69	10/21/1986	3	
	A73	4,798,629	01/17/1989	Wood, et al.	106	287.16	10/22/1987	7	
	A74	4,789,648	12/06/1988	Chow, et al.	438	633	10/28/198	5	
	A75	4,557,946	12/10/1985	Sacher, et al.	427	41	06/03/1983	3	
	A76	4,532,150	07/30/1985	Endo, et al.	427	577	12/22/1983	3	
	A77	4,168,330	09/18/1979	Kaganowicz	427	39	10/13/1977		
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	C15	P. Favia, "Plasma Deposition Of Thin Films From a Fluorine-Containing Cyclosiloxane Journal Of Polymer Science: Part A: Polymer Chemistry, 1992, 10 pp.							
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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	A2	6,524,972	•	02/25/200	3	Maeda	4	38	778	03/09/2000		
	А3	6,475,564		11/05/200	2	Carter, et al.	4	27	249.15	07/06/2000		
	A4	6,242,366	6,242,366		1	Beekman, et al.	4	38	790	02/17/1999		
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	A9	6,140,226		10/31/2000		Grill, et al.	438		637	07/30/1998		
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